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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: MUNNS Examiner: M. WARREN
Serial No.: 10/723,382 Group Art Unit: 2815
Filed: NOVEMBER 25, 2003 Docket: 3165.41USU1
Confirmation No.: 8003
Title: SUPER LATTICE MODIFICATION OF OVERLYING TRANSISTOR

CERTIFICATE UNDER 37 CFR 1.8:

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail, with sufficient postage, in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450 May 11, 2005.

By: 

Name: Kristine A. Wacek

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

23552

PATENT TRADEMARK OFFICE

Sir:

We are transmitting herewith the attached:

- ☒ Transmittal Sheet in duplicate containing Certificate of Mailing
- ☒ Supplemental Information Disclosure Statement, Form 1449, 41 Reference(s)
- ☒ Check(s) in the amount of \$180.00 for filing Supplemental IDS after receipt of Office Action
- ☒ Return postcard

Please consider this a PETITION FOR EXTENSION OF TIME for a sufficient number of months to enter these papers or any future reply, if appropriate. Please charge any additional fees or credit overpayment to Deposit Account No. 13-2725. A duplicate of this sheet is enclosed.

Merchant & Gould P.C.
P.O. Box 2903
Minneapolis, MN 55402-0903
612.332.5300

By: 

Name: Mark DiPietro

Reg. No.: 28,707

MDiPietro:PLSkaw



S/N 10/723,382

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By:

Kristine A. Wacek
Name: Kristine A. Wacek

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT (37 C.F.R. § 1.97(c))

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

23552

PATENT TRADEMARK OFFICE

Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

This statement should be considered because it is submitted after the mailing date of a first Office Action on-the-merits or a first Office Action after filing a Request for Continued Examination under 37 C.F.R. § 1.114 or a CPA under 37 C.F.R. § 1.53(d), but before the mailing date of: i) a final action under 37 C.F.R. § 1.113; ii) a Notice of Allowance under 37 C.F.R. § 1.311; or iii) an action that otherwise closes prosecution on the application. Enclosed is a check in the amount of \$180.00 under 37 C.F.R. § 1.17(p) for consideration of the items listed on the enclosed Form 1449.

A copy of any foreign patent document or "Other Document" listed on the Form 1449 is enclosed, in accordance with 37 C.F.R. § 1.98(a)(2). Because this application was filed after June 30, 2003, copies of the U.S. Patents and U.S. patent publications listed on the enclosed Form 1449 are not provided.

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§ 102 and 103 and Applicants reserve the right, pursuant to 37 C.F.R. § 1.131 or otherwise, to

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establish that the reference(s) are not "prior art." Moreover, Applicants do not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended.

Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.


Please charge any additional fees or credit any overpayment to Deposit Account No. 13-2725.

Respectfully submitted,

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Minneapolis, Minnesota 55402-0903
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Date: 11 May 2005

Mark DiPietro
Mark DiPietro
Reg. No. 28,707
MD:PLSkaw

FORM 1449* INFORMATION DISCLOSURE STATEMENT  IN AN APPLICATION (Use several sheets if necessary)	Docket Number: 3165.41USU1	Application Number: 10/723,382
	Applicant: MUNNS	
	Filing Date: 11/25/2003	Group Art Unit: 2815

/U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	4,300,811	11/17/1981	Ettenberg et al.			
	4,368,098	01/11/1983	Manasevit			
	4,404,265	09/13/1983	Manasevit			
	4,426,656	01/17/1984	DiLorenzo et al.			
	4,471,366	09/11/1984	Delagebeaudeuf et al.			
	4,614,961	09/30/1986	Khan et al.			
	4,616,248	10/07/1986	Khan et al.			
	4,666,250	05/19/1987	Southwell			
	4,999,842	03/12/1991	Huang et al.			
	5,005,057	04/02/1991	Izumiya et al.			
	5,012,486	04/30/1991	Luryi et al.			
	5,052,008	09/24/1991	Kemeny			
	5,146,465	09/08/1992	Khan et al.			
	5,182,670	01/26/1993	Khan et al.			
	5,831,277	11/03/1998	Razeghi			
	5,929,466	07/27/1999	Ohba et al.			
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	5,965,909	10/12/1999	Tanaka			
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	6,177,685 B1	01/23/2001	Teraguchi et al.			
	6,242,765 B1	06/05/2001	Nashimoto			
	6,316,793 B1	11/13/2001	Sheppard et al.			
	6,486,502 B1	11/26/2002	Sheppard et al.			
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EXAMINER	DATE CONSIDERED
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.	

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	6,583,454 B2	06/24/2003	Sheppard et al.			
	6,849,882 B2	02/01/2005	Chavarkar et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	0 297 654 A1	01/04/1989	EP				
	0 549 278 A1	06/30/1993	EP				
	WO 02/093650 A1	11/21/2002	PCT				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	Gaska, R. et al., "Electron transport in AlGaIn-GaN heterostructures grown on 6H-SiC substrates," <i>Applied Physics Letters</i> , Vol. 72, No. 6, pp. 707-709 (February 9, 1998)
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	Hsu, L. et al., "Effect of polarization fields on transport properties in AlGaIn/GaN heterostructures," <i>Journal of Applied Physics</i> , Vol. 89 No. 3, pp. 1783-1789 (February 1, 2001)
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		Khan, M. et al., "Properties and ion implantation of Al _x Ga _{1-x} N epitaxial single crystal films prepared by low pressure metalorganic chemical vapor deposition," <i>Appl. Phys. Lett.</i> , Vol. 43, No. 5, pp. 492-494 (September 1, 1983)
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		Khan, M. et al., "Atomic layer epitaxy of GaN over sapphire using switched metalorganic chemical vapor deposition," <i>Appl. Phys. Lett.</i> , Vol. 60, No. 11, pp. 1366-1368 (March 16, 1992)
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		Monemar, B. et al., "Properties of Zn-doped VPE-grown GaN. I. Luminescence data in relation to doping conditions," <i>J. Appl. Phys.</i> , Vol. 51, No. 1, pp. 625-639 (January 1980)
		Nakamura, S. et al., "Novel metalorganic chemical vapor deposition system for GaN growth," <i>Appl. Phys. Lett.</i> , Vol. 58, No. 18, pp. 2021-2023 (May 6, 1991)
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		Smorchkova, I. et al., "AlN/GaN and (Al,Ga)N/AlN/GaN two-dimensional electron gas structures grown by plasma-assisted molecular-beam epitaxy," <i>Journal of Applied Physics</i> , Vol. 90, No. 10, pp. 5196-5201 (November 15, 2001)
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